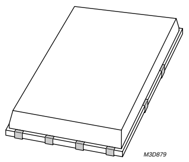


PHM18NQ15T

TrenchMOS™ standard level FET

Rev. 02 — 20 August 2004 **Product data**

1. Product profile

1.1 Description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™ technology.

1.2 Features

- SOT96 (SO-8) footprint compatible
- Surface mounted package
- Low thermal resistance
- Low profile.

1.3 Applications

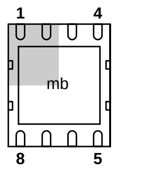
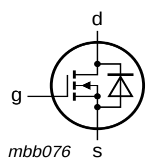
- DC-to-DC converter primary side switch
- Portable equipment applications.

1.4 Quick reference data

- $V_{DS} \leq 150$ V
- $P_{tot} \leq 62.5$ W
- $I_D \leq 19$ A
- $R_{DSon} \leq 75$ mΩ.

2. Pinning information

Table 1: Pinning - SOT685-1 (QLPAK), simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1,2,3	source (s)	 SOT685-1 (QLPAK)	
4	gate (g)		
5,6,7,8	drain (d)		
mb	mounting base; connected to drain (d)		

[1] Shaded area indicates pin 1 identifier.

PHILIPS

3. Ordering information

Table 2: Ordering information

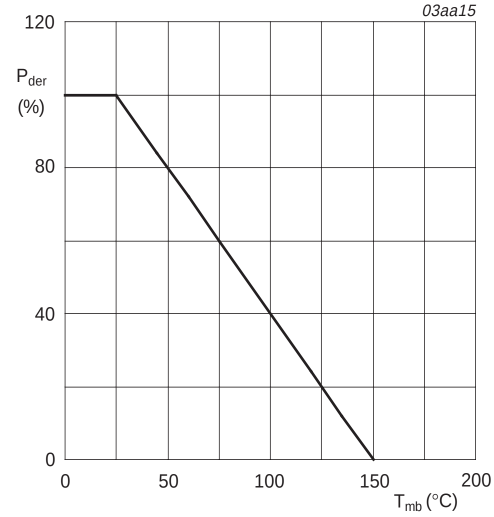
Type number	Package		
	Name	Description	Version
PHM18NQ15T	QLPAK	HVSON8: plastic thermal enhanced very thin small outline package; no leads; 8 terminals; 6 x 5 x 0.85 mm	SOT685-1

4. Limiting values

Table 3: Limiting values

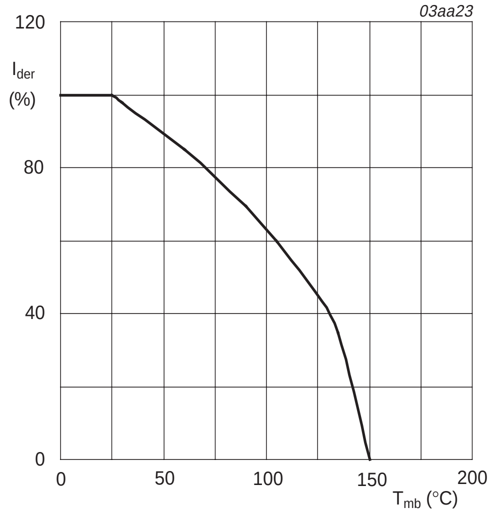
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	25 °C ≤ T_j ≤ 150 °C	-	150	V
V_{DGR}	drain-gate voltage (DC)	25 °C ≤ T_j ≤ 150 °C; R_{GS} = 20 kΩ	-	150	V
V_{GS}	gate-source voltage (DC)		-	±20	V
I_D	drain current (DC)	T_{mb} = 25 °C; V_{GS} = 10 V; Figure 2 and 3	-	19	A
		T_{mb} = 100 °C; V_{GS} = 10 V; Figure 2	-	12	A
I_{DM}	peak drain current	T_{mb} = 25 °C; pulsed; t_p ≤ 10 µs; Figure 3	-	76	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Figure 1	-	62.5	W
T_{stg}	storage temperature		–55	+150	°C
T_j	junction temperature		–55	+150	°C
Source-drain diode					
I_S	source (diode forward) current (DC)	T_{mb} = 25 °C	-	19	A
I_{SM}	peak source (diode forward) current	T_{mb} = 25 °C; pulsed; t_p ≤ 10 µs	-	60	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; I_D = 9.9 A; t_p = 0.16 ms; V_{DD} ≤ 150 V; V_{GS} = 10 V; starting T_j = 25 °C	-	170	mJ



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

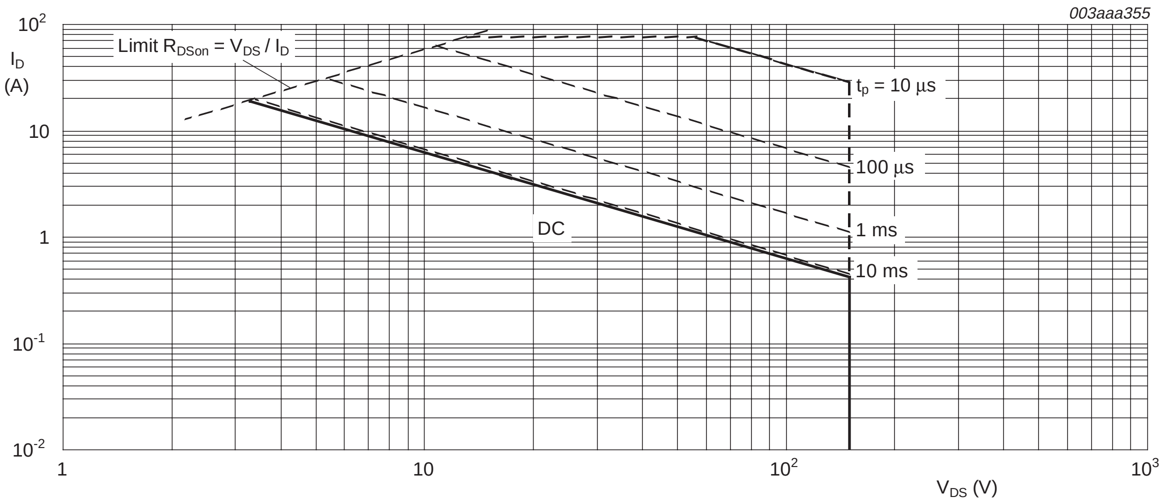
Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$V_{GS} \geq 10$ V

$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of mounting base temperature.



$T_{mb} = 25$ °C; I_{DM} is single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	2	K/W

5.1 Transient thermal impedance

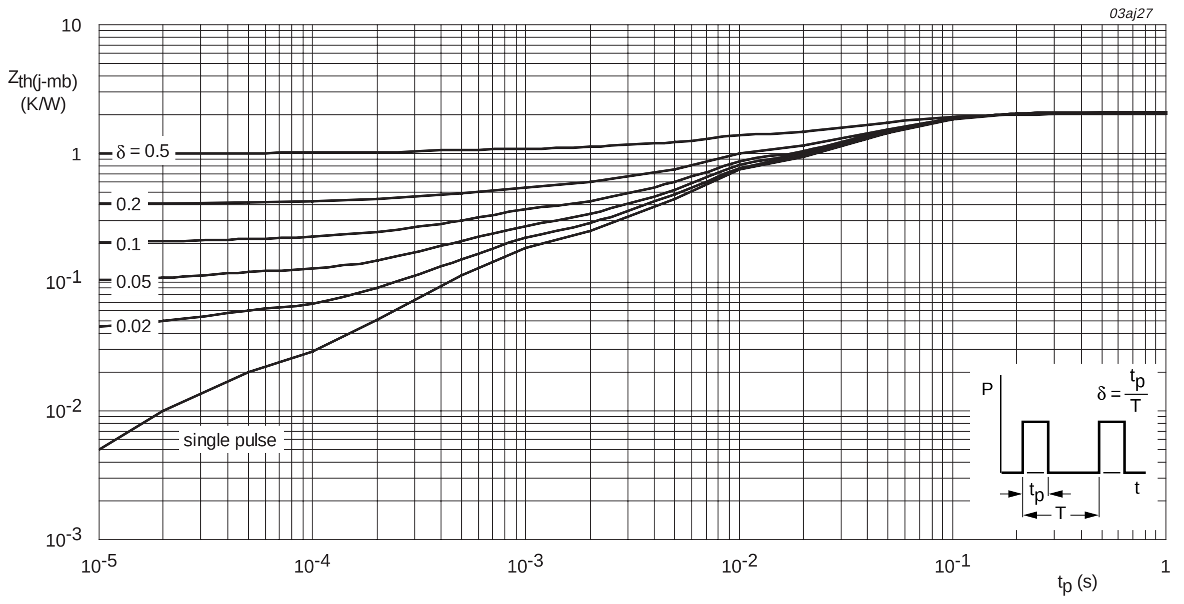


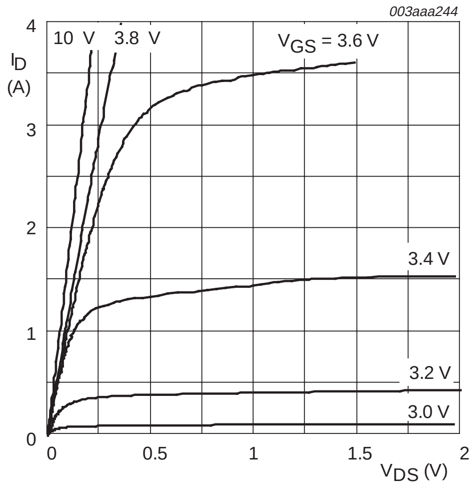
Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.

6. Characteristics

Table 5: Characteristics

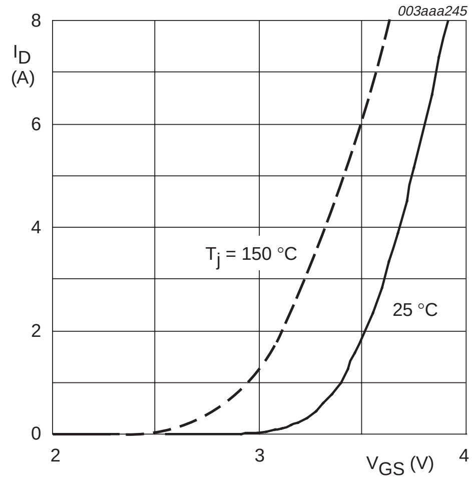
T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V				
		T_j = 25 °C	150	-	-	V
		T_j = –55 °C	134	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; Figure 9				
		T_j = 25 °C	2	3	4	V
		T_j = 150 °C	1.2	-	-	V
		T_j = –55 °C	-	-	4.4	V
I_{DSS}	drain-source leakage current	V_{DS} = 120 V; V_{GS} = 0 V				
		T_j = 25 °C	-	-	1	µA
		T_j = 150 °C	-	-	100	µA
I_{GSS}	gate-source leakage current	V_{GS} = ±10 V; V_{DS} = 0 V	-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 12 A; Figure 7 and 8				
		T_j = 25 °C	-	56	75	mΩ
		T_j = 150 °C	-	129	173	mΩ
		V_{GS} = 5 V; I_D = 3 A; Figure 7 and 8	-	60	80	mΩ
Dynamic characteristics						
$Q_{g(tot)}$	total gate charge	I_D = 5 A; V_{DD} = 75 V; V_{GS} = 10 V; Figure 13	-	26.4	-	nC
Q_{gs}	gate-source charge		-	3.9	-	nC
Q_{gd}	gate-drain (Miller) charge		-	8.8	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; Figure 12	-	1150	-	pF
C_{oss}	output capacitance		-	187	-	pF
C_{rss}	reverse transfer capacitance		-	61	-	pF
$t_{d(on)}$	turn-on delay time	V_{DD} = 75 V; I_D = 5 A; V_{GS} = 10 V; R_G = 6 Ω	-	12	-	ns
t_r	rise time		-	11	-	ns
$t_{d(off)}$	turn-off delay time		-	35	-	ns
t_f	fall time		-	18	-	ns
Source-drain diode						
V_{SD}	source-drain (diode forward) voltage	I_S = 5 A; V_{GS} = 0 V; Figure 11	-	0.76	1.2	V
t_{rr}	reverse recovery time	I_S = 5 A; dI_S/dt = –100 A/µs; V_R = 90 V; V_{GS} = 0 V	-	87	-	ns
Q_r	recovered charge		-	162	-	nC



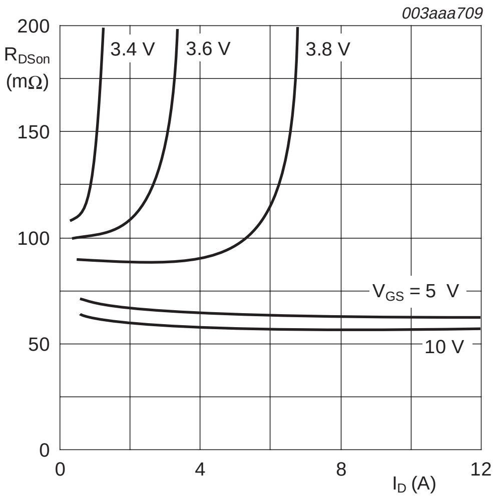
T_j = 25 °C

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



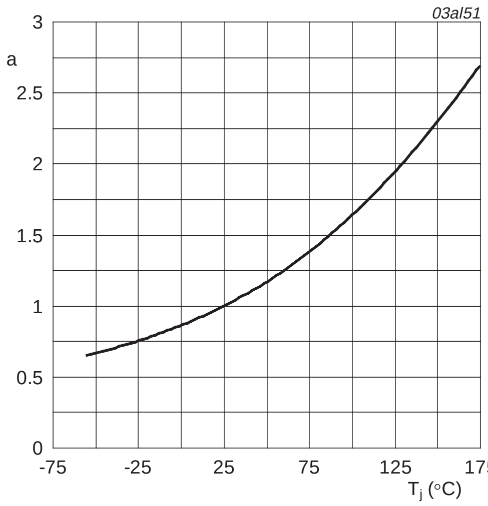
T_j = 25 °C and 150 °C; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



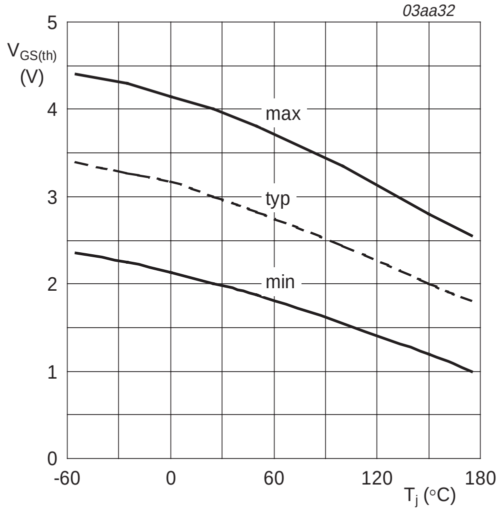
T_j = 25 °C

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



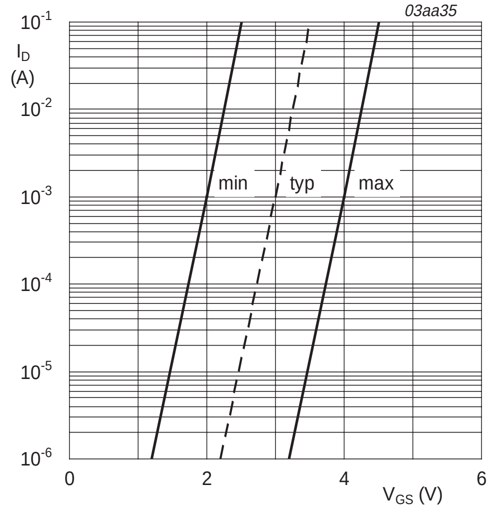
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



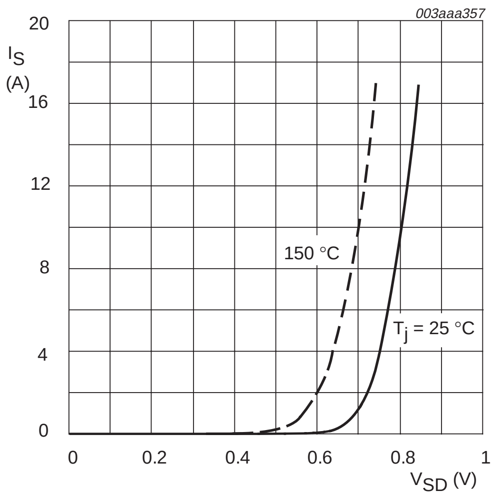
I_D = 1 mA; $V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



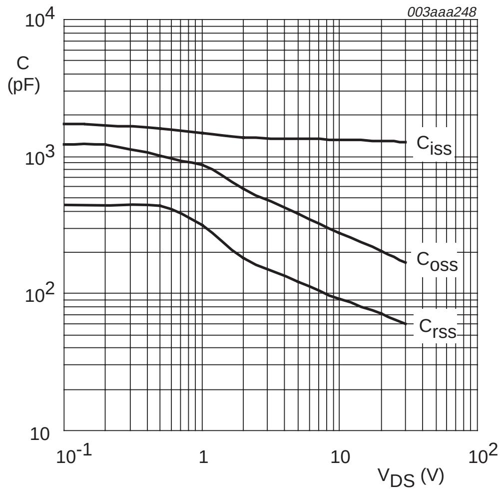
T_j = 25 °C; V_{DS} = 5 V

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



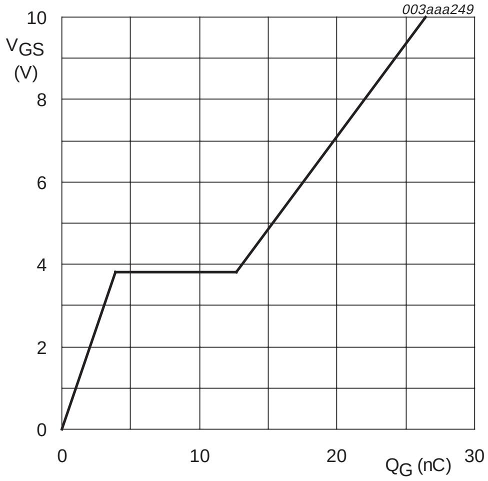
T_j = 25 °C and 150 °C; V_{GS} = 0 V

Fig 11. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



V_{GS} = 0 V; f = 1 MHz

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.

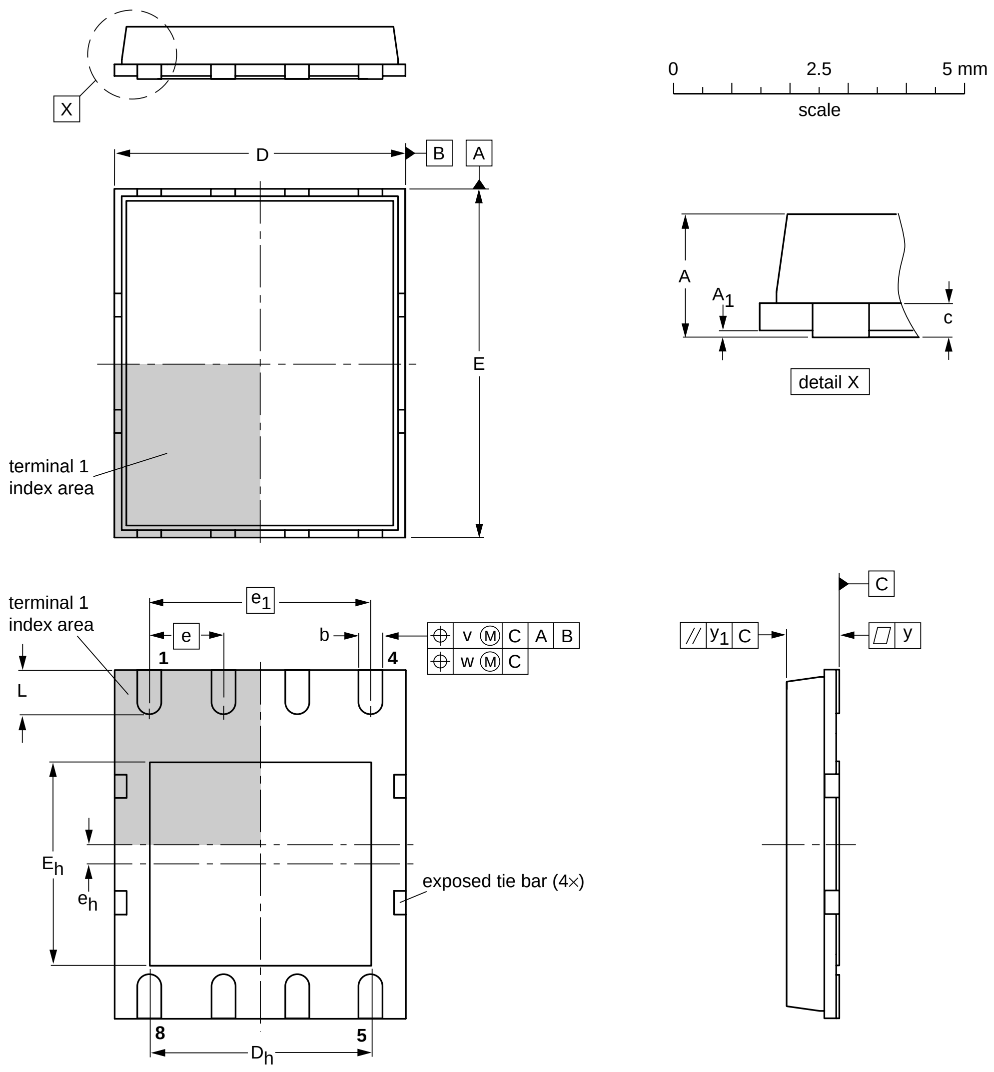


I_D = 5 A; V_{DD} = 75 V

Fig 13. Gate-source voltage as a function of gate charge; typical values.

7. Package outline

HVSON8: plastic thermal enhanced very thin small outline package; no leads; 8 terminals; body 6 x 5 x 0.85 mm **SOT685-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max.	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	e_h	L	v	w	y	y_1
mm	1	0.05 0.00	0.5 0.3	0.2	5.15 4.85	3.95 3.65	6.15 5.85	3.65 3.35	1.27	3.81	0.35	0.75 0.50	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT685-1		- - -				~~02-08-12~~ 02-11-27

Fig 14. SOT685-1 (QLPAK).

8. Revision history

Table 6: Revision history

Rev	Date	CPCN	Description
02	20040820	-	**Product data (9397 750 13865)** Modifications: • Section 1.4 “Quick reference data” I_D data revised. • Section 3 “Ordering information” added to data sheet. • Table 3 “Limiting values” Avalanche ruggedness data added. I_D and I_{DM} data revised. • Figure 3 “Safe operating area; continuous and peak drain currents as a function of drain-source voltage.” revised. • Table 5 “Characteristics” Q_r data added, $Q_{g(tot)}$, Q_{gs} and Q_{gd} data corrected. • Figure 7 “Drain-source on-state resistance as a function of drain current; typical values.” revised.
01	20030130	-	**Preliminary data (9397 750 10877)**

9. Data sheet status

Level	Data sheet status[1]	Product status[2][3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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